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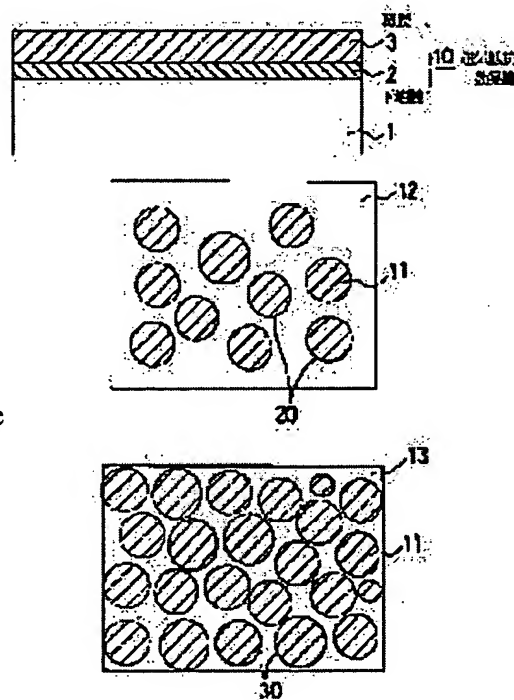
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(54) MAGNETORESISTIVE EFFECT FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a magnetoresistive effect film which enables positive control of the crystal grain size and form of a magnetic phase grain, a non- magnetic phase matrix or an insulating phase matrix, and which enables obtaining a large magnetoresistive effect even in the case of a granular structure.

SOLUTION: This film 10 is formed by stacking a thin film 3 containing a magnetic phase grain 11 in a non-magnetic phase matrix 12 or an insulating phase matrix 13 onto an underlying film 2. In this case, the underlying film 2 is made of Ti or Al, and the non-magnetic phase matrix 12 is made of Ti or Al. The magnetic phase grain 11 is made of at least one of Fe, Ni and Co.



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